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- (54) **Title:** SELECTIVE DEPOSITION OF ALUMINUM-CONTAINING DIELECTRIC MATERIAL ON DIELECTRIC OVER METALS UTILIZING SILANES

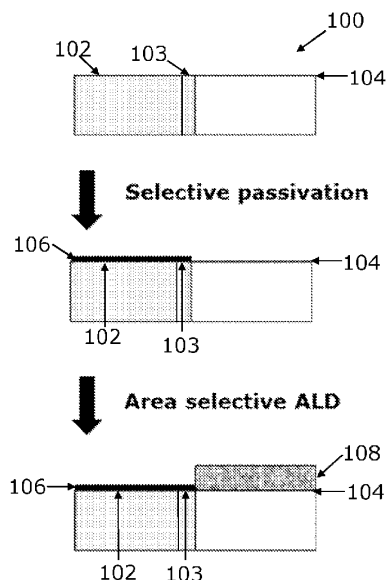


FIG. 1

- (57) **Abstract:** A method for selectively passivating a substrate, wherein the substrate includes at a first surface comprising a first metal and at least a second surface comprising a second metal, preferably a metal nitride, and a third surface comprising a dielectric material. The method includes the step of exposing the substrate to at least one silane wherein the silane selectively reacts with the first surface and the second surface to passivate the first surface and the second surface thereby leaving the third surface substantially unreacted.

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